L Number	Hits	Search Text	DB	Time stamp
1	60	(semiconductor near laser) and faces and (cavity	USPAT;	2003/06/25 12:48
		near3 length) and (QW or (quantum near well)) and	US-PGPUB;	
		(reflect\$6 near2 low\$3) and (reflect\$6 near2 higH)	EPO; JPO;	
		_	DERWENT;	
			IBM TDB	
-	768	(semiconductor near laser) and (active near (layer or	USPAT;	2002/06/14 16:26
		region or medium or film)) and (quantum near well or	US-PGPUB;	
		qw) and (mirror or ((low and high) near reflect\$))	EPO; JPO;	
		and 372/\$	DERWENT;	
			IBM TDB	
_	260	((semiconductor near laser) and (active near (layer or	USPAT;	2001/11/29 18:04
	200	region or medium or film)) and (quantum near well or	US-PGPUB;	2001/11/25 10.04
		qw) and (mirror or ((low and high) near reflect\$))	EPO; JPO;	
		and 372/\$) and 372/96	· ·	
		and 3/2/9) and 3/2/96	DERWENT;	
		Managina de atau a santina A a a talanta di	IBM_TDB	0004144100 40 05
-	11	(((semiconductor near laser) and (active near (layer or	USPAT;	2001/11/29 18:05
		region or medium or film)) and (quantum near well or	US-PGPUB;	
-		qw) and (mirror or ((low and high) near reflect\$))	EPO; JPO;	
		and 372/\$) and 372/96) and (laminat\$ near	DERWENT;	
		structure)	IBM_TDB	
-	4	(semiconductor near laser) and (active near (layer or	USPAT;	2002/06/14 16:28
		region or medium or film)) and (quantum near well or	US-PGPUB;	
		qw) and ((low and high) near reflect\$) and 372/\$	EPO; JPO;	
		and (laminat\$ near structure)	DERWENT;	
			IBM TDB	
_	4	((semiconductor near laser) and (active near (layer or	USPAT;	2001/11/29 18:19
		region or medium or film) SAME (quantum near well	US-PGPUB;	-55171172515116
1		or qw)) and ((low and high) near reflect\$) and	EPO; JPO;	
		(laminat\$ near structure)) and 372/\$	DERWENT;	v
		transmitter from our doctor of f und of 214	IBM TDB	
_	5	(semiconductor near laser) and (active near (layer or	USPAT;	2001/11/29 19:24
	J	region or medium or film) SAME (quantum near well	US-PGPUB;	2001/11/29 19.24
		or qw)) and ((low and high) near reflect\$) and	EPO; JPO;	
İ		(laminat\$ near structure)	DERWENT;	
		(laminaty near structure)		
_	73	(comiconductor poor locar) and (cotive cons (lover or	IBM_TDB	0004/44/00 40.07
-	/3	(semiconductor near laser) and (active near (layer or	USPAT;	2001/11/29 19:27
		region or medium or film) SAME (quantum near well	US-PGPUB;	
		or qw)) and ((low and high) near reflect\$)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1	(semiconductor near laser) and (active near (layer or	USPAT;	2001/11/29 19:27
		region or medium or film) SAME (quantum near well	US-PGPUB;	
1		or qw)) and ((low and high) near mirror) and	EPO; JPO;	
		(laminat\$ near structure)	DERWENT;	
			IBM_TDB	
-	56	((semiconductor near laser) and (active near (layer or	USPAT;	2001/11/29 19:28
		region or medium or film) SAME (quantum near well	US-PGPUB;	
		or qw)) and ((low and high) near reflect\$)) and	EPO; JPO;	
		372/\$	DERWENT;	
			IBM TDB	
-	4	(semiconductor near laser) and (active near (layer or	USPAT;	2001/11/29 19:42
		region or medium or film) SAME (quantum near well	US-PGPUB;	2001/11/23 13.42
		or qw)) and ((low and high) near mirror)	EPO; JPO;	
		or goog and most ingit treat military		
			DERWENT;	
	1		IBM_TDB	

Pegion or medium or film) and (quantum near well or qw) and film/ror or (flow and high) near reflect(\$1) DERWENT; IBM, TDB uSPAT: u					
aw) and (mirror or ((low and high) near reflect\$) and substrate DERWENT; IBM, TDB USPAT; USPAT; IBM, TDB USPAT; USPAT; IBM, TDB USPAT; US	-	1093	1	USPAT;	2002/06/14 16:36
and substrate semiconductor near laser) and (active near (layer or region or medium or film!) and (quantum near well or qw) and (low near reflect\$5) and (substrate) Semiconductor near laser) and (active near (layer or region or medium or film)) and (quantum near well or qw) and (low near reflect\$5) and substrate Semiconductor near laser) and (active near (layer or region or medium or film)) and (quantum near well or qw) and (low near reflect\$5) and substrate) and cavity Semiconductor near laser) and (active near (layer or region or medium or film)) and (quantum near well or qw) and (low near reflect\$5) and substrate) and (active near (layer or region or medium or film)) and (quantum near well or qw) and (low and low near reflect\$5) and substrate) and (active near (layer or region or medium or film)) and (quantum near well or qw) and (low and high) near reflect\$1 and substrate Semiconductor near laser) with (optical near fibert) and (active near (layer or region or medium or film) Semiconductor near laser) and faces and cavity and (QW or (quantum near well)) and (reflect\$6 near2 (low or high!)) Semiconductor near laser) and faces and cavity and (QW or (quantum near well.)) and (reflect\$6 near2 (low or high!)) Semiconductor near laser) and faces and cavity and (QW or (quantum near well.)) and (reflect\$6 near2 (low or high!)) Semiconductor near laser) and faces and cavity and (QW or (quantum near well.)) and (reflect\$6 near2 (low or high!)) Semiconductor near laser) and faces and cavity and (QW or (quantum near well.)) and (reflect\$6 near2 (low or high!)) Semiconductor near laser) and faces and cavity and (lactive near (medium or region or film or layer)) with (QW or (quantum near well)) Semiconductor near laser) and faces and cavity and (lactive near (medium or region or film or layer)) with (QW or (quantum near well)) Semiconductor near laser) and faces and (cavity near3 length) and (lactive near (medium or region or film or layer)) with (QW or (quantum near well)) Semiconductor nea	-	1		1	
BM TDB Semiconductor near laser) and (active near (layer or region or medium or film)) and (quantum near well or qw) and (low near reflect\$5) and high near reflect\$5) SPAT: US-PGPUB; PRO; JPO; DERWENT; BIM TDB SPAT: qw) and (low near reflect\$5) and (active near (layer or region or medium or film)) and (quantum near well or qw) and (low near reflect\$5) and substrate) and cavity near (layer or region or medium or film)) and (quantum near well or qw) and (low near reflect\$5) and (substrate) and (cavity near 2 length) SPAT; gwo yand (low near reflect\$5) and (low near reflect\$5) and substrate) and (cavity near 2 length) SPAT; gwo yand (low near reflect\$5) and (low near (layer or region or medium or film)) and (acuntum near well or qw) and (low near (layer) or ("5337291"),PN. SPAT; gwo yand (low or qw) and (low near (layer) or ("5337291"),PN. SPAT; gwo yand (low or qw) and (low near (layer) or ("5337291"),PN. Semiconductor near laser) and faces and cavity and (QW or (quantum near weell)) and (reflect\$6 near 2 (low or high!)) SPAT; gwo yand (low or high!) SPAT; gwo yand (low yand yand yand yand yand yand yand yand			qw) and (mirror or ((low and high) near reflect\$))	EPO; JPO;	
Semiconductor near laser) and (active near (layer or qw) and (low near reflect\$5) and substrate Semiconductor near laser) and (active near (layer or qw) and (low near reflect\$5) and (low near reflect\$5) and substrate Semiconductor near laser) and (active near (layer or region or medium or film)) and (quantum near well or qw) and (low near reflect\$5) and (high near reflect\$5) and substrate Semiconductor near laser) and (active near (layer or region or medium or film)) and (quantum near well or qw) and work near reflect\$5) and substrate Semiconductor near laser) and (active near (layer or region or medium or film)) and (active near (leyer or region or medium or film)) and (active near (leyer or region or medium or film)) and (active near (leyer or region or medium or film)) and (active near (leyer or region or medium or film)) and (active near (leyer or region or medium or film)) and (active near (leyer or region or medium or film)) and (active near (leyer or region or medium or film)) and (active near (leyer or region or medium or film)) and (active near (leyer or region or medium or film) and (active near (leyer or region or medium or region or film or layer)) Ph. USPAT; USP-GPUB; EPO; JPO; DERWENT; IBM, TDB USP-GPUB; EPO; JPO			and substrate	DERWENT;	
region or medium or film)) and (quantum near well or qw) and (low near reflect\$5) and substrate 113	İ	•		IBM_TDB	
qw and (low near reflect\$5) and substrate EPC, JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; E	-	186	(semiconductor near laser) and (active near (layer or	USPAT;	2002/06/14 16:48
113			region or medium or film)) and (quantum near well or	US-PGPUB;	
and substrate ((semiconductor near laser) and (active near (layer or region or medium or film)) and (quantum near well or qw) and (low near reflect\$5) and substrate) and (active near (layer or region or medium or film)) and (quantum near well or qw) and (low near reflect\$5) and substrate) and (active near (layer or region or medium or film)) and (quantum near well or qw) and (low near reflect\$5) and substrate) and (active near (layer or region or medium or film)) and (active near (layer or region or medium or film)) and (quantum near well or qw) and (low and high) near reflect\$) and substrate 4 (("4651322") or ("4731792") or ("5870417") or ("5337231")).PN. 1 ("5337231").PN. 1 ("5337231").PN. 2 ((semiconductor near laser) and faces and cavity and (QW or (quantum near well)) and (reflect\$6 near2 (low or high))) nd (reflect\$6 near2 (low or high))) and (reflect\$6 near2 (low or high)) and (refl			qw) and (low near reflect\$5) and (high near reflect\$5)	EPO; JPO:	
IBM_TDB			1 ·		
113					
region or medium or film!) and (quantum near well or qw) and (low near reflect\$5) and substrate) and cavity 63 ((semiconductor near laser) and (active near (layer or region or medium or film!) and (quantum near well or qw) and (low near reflect\$5) and substrate) and (cavity near2 length) 43 ((semiconductor near laser) with (optical near fiber)) and (settive near (layer or region or medium or film)) and (quantum near well or qw) and (low near reflect\$5) and substrate) and (cavity near2 length) 43 ((semiconductor near laser) with (optical near fiber)) and (active near (layer or region or medium or film)) and (quantum near well or qw) and ((low and high)) near reflect\$) and substrate 4 (("4651322") or ("4731792") or ("5870417") or ("5337229");PN. 5 ((semiconductor near laser) and faces and cavity and (QW or (quantum near weell)) and (reflect\$6 near2 (low or high!)) 6 (semiconductor near laser) and faces and cavity and (QW or (quantum near weell)) and (reflect\$6 near2 (low or high!))) AND (active near (medium or region or film or layer)) with (QW or (quantum near wetl!)) and (reflect\$6 near2 (low or high!))) AND (active near (medium or region or film or layer)) with (QW or (quantum near wetl!)) and (reflect\$6 near2 (low or high!)) and (reflect\$6 near2 (low\$8)) and (reflect\$6 near2 (low\$8)) and (reflect\$6 near2 (low\$8))	_	113	((semiconductor near laser) and (active near (layer or		2002/06/14 17:25
aw) and llow near reflect\$5] and (high near reflect\$5] and substrate) and cavity DERWENT; BM_TDB USPAT; USP-GPUB; EPO; JPO; DERWENT; BM_TDB USPAT; USPAT			,	1	2002/00/14 17.25
and substrate) and cavity ((semiconductor near laser) and (active near (layer or region or medium or film)) and (quantum near well or qw) and (low near reflect\$) and substratel and (cavity near2 length) 43 ((semiconductor near laser) with (optical near fiber)) and (active near (layer or region or medium or film)) and (quantum near well or qw) and (low and high) near reflect\$) and substrate 43 ((semiconductor near laser) with (optical near fiber)) and (quantum near well or qw) and ((low and high)) near reflect\$) and substrate 4 (("4651322") or ("4731792") or ("5870417") or ("5337291").PN 5 (("5337291").PN 6 (semiconductor near laser) and faces and cavity and (QW or (quantum near weell)) and (reflect\$6 near2 (low or high)) 6 (semiconductor near laser) and faces and cavity and (QW or (quantum near weell)) and (reflect\$6 near2 (low or high))) 7 ((semiconductor near laser) and faces and cavity and (QW or (quantum near weell)) and (reflect\$6 near2 (low or high))) 8 (semiconductor near laser) and faces and cavity and ((active near (medium or region or film or layer)) with (QW or (quantum near well))) and (reflect\$6 near2 (low or high))) 9 (semiconductor near laser) and faces and cavity and ((active near (medium or region or film or layer)) with (QW or (quantum near well))) and (reflect\$6 near2 (low or high)) 131 (semiconductor near laser) and faces and cavity and ((active near (medium or region or film or layer)) with (QW or (quantum near well))) and (reflect\$6 near2 (low or high)) 143 (semiconductor near laser) and faces and cavity and ((active near (medium or region or film or layer)) with (QW or (quantum near well))) and (reflect\$6 near2 (low or high)) 154 (semiconductor near laser) and faces and cavity and (reflect\$6 near2 (low or high)) 155 (semiconductor near laser) and faces and cavity and (reflect\$6 near2 (low or high)) 156 (semiconductor near laser) and faces and cavity and (reflect\$6 near2 (low or high)) 157 (low or high) 157 (low or high) 158 (semiconductor near laser) and faces and (cavit				1	
193 ((semiconductor near laser) and (active near (layer or region or medium or film)) and (quantum near well or qw) and (low near reflect\$5) and (high near reflect\$5) and (substrate) and (cavity near2 length) and (active near (layer or region or medium or film)) and (quantum near well or qw) and (low and high) near reflect\$1) and active near (layer or region or medium or film)) and (quantum near well or qw) and ((low and high) near reflect\$1) and substrate 4					
Clsemiconductor near laser) and factive near (layer or region or medium or film) and (quantum near well or qw) and (low near reflect\$5) and substrate) and (cavity near2 length) Clsemiconductor near laser) with (optical near fiber) Clsemiconductor near laser) with (optical near fiber) Clsemiconductor near laser) and faces and cavity and (low or high!) Clsemiconductor near laser) and faces and cavity and (OW or (quantum near well)) and (reflect\$6 near2 (low or high!)) Clsemiconductor near laser) and faces and cavity and (OW or (quantum near well)) and (reflect\$6 near2 (low or high!)) Clsemiconductor near laser) and faces and cavity and (OW or (quantum near well)) and (reflect\$6 near2 (low or high!)) Clsemiconductor near laser) and faces and cavity and (OW or (quantum near well)) and (reflect\$6 near2 (low or high!)) Clsemiconductor near laser) Cls			and substrate, and cavity		
region or medium or film!) and (quantum near well or qw) and (low near reflect\$5) and (high near reflect\$5) and substrate) and (cavity near2 length) ((semiconductor near laser) with (optical near fiber.)) and (active near (layer or region or medium or film)) and (quantum near well or qw) and ((low and high)) near reflect\$1 and substrate) (("4651322") or ("4731792") or ("5870417") or ("537291").PN. ("5337291").PN. ("5337291").PN. ("5377291").PN. ((semiconductor near laser) and faces and cavity and (QW or (quantum near weell)) and (reflection near2) (low or high!) (semiconductor near laser) and faces and cavity and (QW or (quantum near well.)) and (reflect\$6 near2) (low or high!)) ((semiconductor near laser) and faces and cavity and (QW or (quantum near well.)) and (reflect\$6 near2) (low or high!)) ((semiconductor near laser) and faces and cavity and (QW or (quantum near well.)) and (reflect\$6 near2) (low or high!)) ((semiconductor near laser) and faces and cavity and (QW or (quantum near well.)) and (reflect\$6 near2) (low or high!)) ((semiconductor near laser) and faces and cavity and ((active near (medium or region or film or layer)) with (QW or (quantum near well.)) and (reflect\$6 near2) (low or high!)) ((semiconductor near laser) and faces and cavity and ((active near (medium or region or film or layer)) with (QW or (quantum near well.)) and (reflect\$6 near2) (low or high!)) (semiconductor near laser) and faces and cavity and ((active near (medium or region or film or layer)) with (QW or (quantum near well)) and (reflect\$6 near2) (low or high!) (semiconductor near laser) and faces and (cavity near3 length) and ((active near (medium or region or film or layer)) with (QW or (quantum near well)) and (reflect\$6 near2) (low or high!) (semiconductor near laser) and faces and (cavity near3 length) and ((active near (medium or region or film or layer)) with (QW or (quantum near well)) and (reflect\$6 near2) (low or high!) (semiconductor near laser) and faces and (cavity near3 length) and (lactive near		62	(looming and uptor and loom) and (notice and (loom)		0000/00/4 4 7 00
qwi and (low near reflect\$5) and (high near reflect\$5) EPC; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPC; JPO; DERWENT; IBM_TDB USPAT; USPAT; USPAT	-	03			2002/06/14 17:26
and substrate) and (cavity near2 length) ((semiconductor near laser) with (optical near fiber)) and (active near (layer or region or medium or film)) and (active near (layer or region or medium or film)) and (active near (layer or region or medium or film)) and (active near (layer or region or medium or film)) and (active near (layer or region or medium or film)) and (querter) (("4651322") or ("4731792") or ("5870417") or ("5337291").PN. (("5337291").PN. (("5337291").PN. ((semiconductor near laser) and faces and cavity and (QW or (quantum near weell)) and (reflects near2 (low or high)) ((semiconductor near laser) and faces and cavity and (QW or (quantum near well)) and (reflects near2 (low or high)) ((semiconductor near laser) and faces and cavity and (QW or (quantum near well)) and (reflects near2 (low or high)) ((semiconductor near laser) and faces and cavity and (QW or (quantum near well)) and (reflects near2 (low or high)) ((semiconductor near laser) and faces and cavity and (lactive near (medium or region or film or layer)) ((semiconductor near laser) and faces and cavity and (lactive near (medium or region or film or layer)) with (QW or (quantum near well)) and (reflects near2 (low or high)) ((semiconductor near laser) and faces and (cavity near3 length) and (lactive near (medium or region or film or layer)) with (QW or (quantum near well)) and (reflects near2 (low or high)) ((semiconductor near laser) and faces and (cavity near3 length) and (lactive near (medium or region or film or layer)) with (QW or (quantum near well)) and (reflects near2 (low or high)) ((semiconductor near laser) and faces and (cavity near3 length) and (lactive near (medium or region or film or layer)) with (QW or (quantum near well)) and (reflects near2 (low shigh)) (semiconductor near laser) and faces and (cavity near3 length) and (lactive near (medium or region or film or layer)) with (-	
43				1	
43 ((semiconductor near laser) with (optical near fiber)) and (active near (layer or region or medium or film)) and (active near (layer or region or medium or film)) and (active near (layer or region or medium or film)) near reflect\$) and substrate 4 (("4651322") or ("4731792") or ("5870417") or ("5377291").PN.			and substrate) and (cavity near2 length)	1	
and (active near (layer or region or medium or film)) and (quantum near well or qw) and ((low and high) near reflect\$) and substrate 4 (("4651322") or ("4731792") or ("5870417") or ("5337291")).PN. 1 ("5337291").PN. 2 (Semiconductor near laser) and faces and cavity and (CW or (quantum near well)) and (reflect\$6 near2 (low or high!)) 3 (Semiconductor near laser) and faces and cavity and (CW or (quantum near well)) and (reflect\$6 near2 (low or high!)) AND (active near (medium or region or film or layer)) 3 (Semiconductor near laser) and faces and cavity and (CW or (quantum near well)) and (reflect\$6 near2 (low or high!)) AND (active near (medium or region or film or layer)) 4 (Semiconductor near laser) and faces and cavity and (CW or (quantum near well))) and (reflect\$6 near2 (low or high!)) AND (active near (medium or region or film or layer)) 5 (Semiconductor near laser) and faces and cavity and (lactive near (medium or region or film or layer)) with (CW or (quantum near well))) and (reflect\$6 near2 (low or high!)) 5 (Semiconductor near laser) and faces and (cavity near3 length) and ((active near (medium or region or film or layer)) with (CW or (quantum near well))) and (reflect\$6 near2 (low or high!)) 5 (Semiconductor near laser) and faces and (cavity near3 length) and ((active near (medium or region or film or layer)) with (CW or (quantum near well))) and (reflect\$6 near2 (low or high!)) 5 (Semiconductor near laser) and faces and (cavity near3 length) and ((active near (medium or region or film or layer)) with (CW or (quantum near well))) and (reflect\$6 near2 (low or high!)) 6 (Semiconductor near laser) and faces and (cavity near3 length) and ((active near (medium or region or film or layer)) with (CW or (quantum near well))) and (reflect\$6 near2 (low\$3)) and (reflect\$6 near2 (high\$4] 5 (Semiconductor near laser) and faces and (cavity near3 length) and (reflect\$6 near2 (high\$4] 6 (Semiconductor near laser) and faces and (cavity near3 length) and (reflect\$6 near2 (high\$4] 6 (Semiconductor near la					
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and (quantum near well or qw) and ((low and high) near reflect\$) and substrate 4 (("4651322") or ("4731792") or ("5870417") or ("5377291").PN. 1 ("5377291").PN. 1 ("5377291").PN. 2 (semiconductor near laser) and faces and cavity and (QW or (quantum near well)) and (reflection near2 (low or high)) 3 (semiconductor near laser) and faces and cavity and (QW or (quantum near well)) and (reflect\$6 near2 (low or high)) 4 ((semiconductor near laser) and faces and cavity and (QW or (quantum near well)) and (reflect\$6 near2 (low or high)) 5 (semiconductor near laser) and faces and cavity and (lactive near (medium or region or film or layer)) 6 (semiconductor near laser) and faces and cavity and (lactive near (medium or region or film or layer)) 7 (semiconductor near laser) and faces and cavity and (lactive near (medium or region or film or layer)) with (QW or (quantum near well)) and (reflect\$6 near2 (low or high)) 8 (semiconductor near laser) and faces and (cavity near3 length) and (lactive near (medium or region or film or layer)) with (QW or (quantum near well))) and (reflect\$6 near2 (low or high)) 9 (semiconductor near laser) and faces and (cavity near3 length) and (lactive near (medium or region or film or layer)) with (QW or (quantum near well))) and (reflect\$6 near2 (low or high)) 13 (semiconductor near laser) and faces and (cavity near3 length) and (lactive near (medium or region or film or layer)) with (QW or (quantum near well))) and (reflect\$6 near2 (low\$3)) and (reflect\$6 near2 (low\$3)) and (reflect\$6 near2 (low\$4)) and (reflect\$6 near2 (low\$4)) and (reflect\$6 near2 (low\$4)) and (reflect\$6 near2 (low\$5)) and (reflect\$6 near2 (low\$6)) and (refle			and (active near (layer or region or medium or film))	US-PGPUB;	
near reflect\$) and substrate				EPO; JPO;	
1					
- ("4651322") or ("4731792") or ("5870417") or ("537291").PN. - 1 ("5377291").PN. - 0 (semiconductor near laser) and faces and cavity and (QW or (quantum near weell)) and (reflection near2 (low or high)) - 193 (semiconductor near laser) and faces and cavity and (QW or (quantum near weLl)) and (reflect\$6 near2 (low or high)) - 173 ((semiconductor near laser) and faces and cavity and (QW or (quantum near weLl)) and (reflect\$6 near2 (low or high)) - 131 (semiconductor near laser) and faces and cavity and ((active near (medium or region or film or layer)) with (QW or (quantum near weLl)) and (reflect\$6 near2 (low or high!)) - 131 (semiconductor near laser) and faces and cavity and ((active near (medium or region or film or layer)) with (QW or (quantum near weLl))) and (reflect\$6 near2 (low or high!)) -				1	
1	-	4	(("4651322") or ("4731792") or ("5870417") or		2003/01/12 13:07
1					
(a) (semiconductor near laser) and faces and cavity and (a) (a) (quantum near weel)) and (reflection near) (a) (b) (b) (b) (c) (c) (d) (d) (d) (d) (d) (e) (e) (e) (e) (e) (e) (e) (e) (e) (e	-	1		LISPAT	2003/01/12 13:14
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